

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China









TPR 400

400 Watts, 50 Volts, Pulsed Avionics 1030 - 1090 MHz

GENERAL DESCRIPTION

The TPR 400 is a high power COMMON BASE bipolar transistor. It is designed for pulsed systems in the frequency band 1030-1090 MHz. The device has gold thin-film metallization for proven highest MTTF. The transistor includes input prematch for broadband capability. Low thermal resistance package reduces junction temperature, extends life.

ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation @ 25°C² 875 Watts

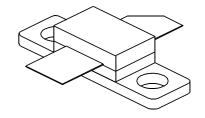
Maximum Voltage and Current

BVcesCollector to Base Voltage55 VoltsBVeboEmitter to Base Voltage4.0 VoltsIcCollector Current30 Amps

Maximum Temperatures

Storage Temperature $-65 \text{ to} + 150^{\circ}\text{C}$ Operating Junction Temperature $+200^{\circ}\text{C}$

CASE OUTLINE 55CX, STYLE 1



ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Pout Pin Pg η _c	Power Out Power Input Power Gain Collector Efficiency	F = 1030-1090 MHz Vcc = 50 Volts PW = 10 µsec DF = 1%	400 7.27	40	75	Watts Watts dB %
VSWR	Load Mismatch Tolerance	F = 1090 MHz			20:1	

BVebo BVces	Emitter to Base Breakdown Collector to Emitter Breakdown	Ie = 20 mA Ic = 25 mA	4.0 55		Volts Volts
$egin{array}{c} \mathbf{h_{FE}} \\ \mathbf{ heta jc^2} \end{array}$	DC - Current Gain Thermal Resistance	Ic = 2.5 A, Vce = 5 V	10	100 0.2	°C/W

Note 1: At rated output power and pulse conditions

2: At rated pulse conditions

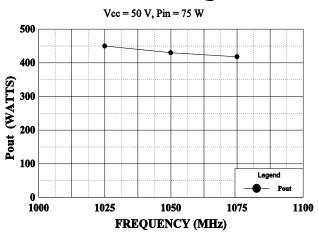
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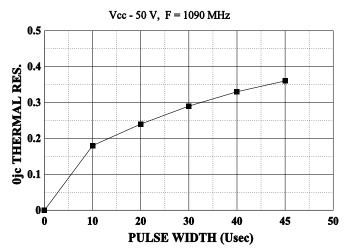
CHz TECHNOLOCY RF-MIGROWAVE SILICON POWER TRANSISTORS

TPR400

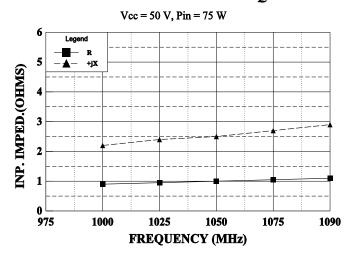
POWER OUTPUT vs FREQUENCY



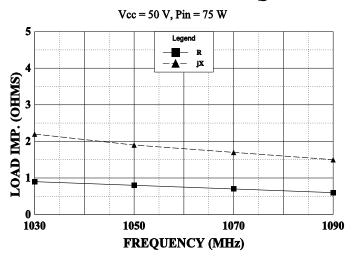
THERMAL RESISTANCE vs PULSE WIDTH



SERIES INPUT IMPEDANCE vs FREQUENCY

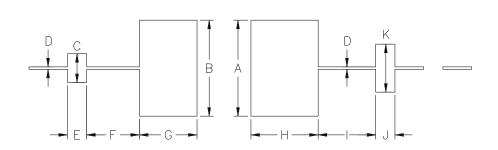


SERIES LOAD IMPEDANCE vs FREQUENCY



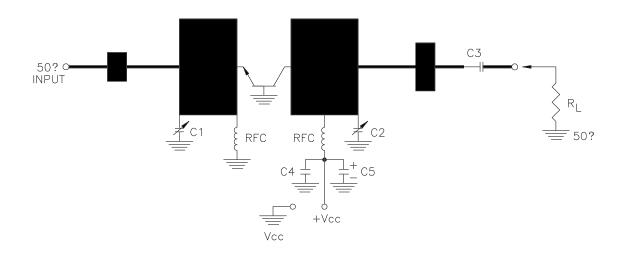


REVISIONS				
ZONE	REV	DESCRIPTION	DATE	APPROVED



DIM	INCHES
Α	1.000
В	1.000
С	.300
D	.025
Ε	.200
F	.550
G	.600
Η	.700
- 1	.600
J	.200
K	.500

DME 375 / TPR 400 TEST FIXTURE 1030/1090 MHz - TEST AMPLIFIER (FIG1)



MICROSTRIP LINE: DUROID, 10 MIL DIELECTRIC D 5880

C1, C2 - 0.6-6pf VAR. CAP. C3, C4 - 82 pf CHIP C5 - 200 MFD CAP.



GHz TECHNOLOGY

CAGE	DWG NO.			REV
0PJR2	DME	375 / T	PR 400	_
	SCALE	1/1	SHEET	